

Додаткову інформацію щодо як розглянутих методів, так і низки інших можна знайти в [1–10].

Рекомендована та використана література

- [1] *Cai, Xuefen*. Perspective on defect control in semiconductors for photovoltaics / Xuefen Cai, Su-Huai Wei // *J. Appl. Phys.* — 2023. — Dec. — Vol. 134, no. 22. — P. 220901.
- [2] Iron-boron pairing kinetics in illuminated p-type and in boron/phosphorus co-doped n-type silicon / Christian Möller, Til Bartel, Fabien Gibaja, Kevin Lauer // *J. Appl. Phys.* — 2014. — Jul. — Vol. 116, no. 2. — P. 024503.
- [3] The Role of Charge and Recombination-Enhanced Defect Reaction Effects in the Dissociation of FeB Pairs in p-Type Silicon under Carrier Injection / Chang Sun, Yan Zhu, Mattias Juhl et al. // *Phys. Status Solidi RRL*. — 2021. — Dec. — Vol. 15, no. 12. — P. 2000520.
- [4] Reassessing iron–gallium recombination activity in silicon / Tien T. Le, Zhuangyi Zhou, Alan Chen et al. // *J. Appl. Phys.* — 2024. — Apr. — Vol. 135, no. 13. — P. 133107.
- [5] Iron–boron pair dissociation in silicon under strong illumination / Xiaodong Zhu, Deren Yang, Xuegong Yu et al. // *AIP Adv.* — 2013. — Aug. — Vol. 3, no. 8. — P. 082124.
- [6] Dissociation and Formation Kinetics of Iron–Boron Pairs in Silicon after Phosphorus Implantation Gettering / Nabil Khelifati, Hannu S. Laine, Ville Vähänissi et al. // *Phys Status Solidi A*. — 2019. — Sep. — Vol. 216, no. 17. — P. 1900253.
- [7] *Geerligs, L. J.* Dynamics of light-induced FeB pair dissociation in crystalline silicon / L. J. Geerligs, Daniel Macdonald // *Appl. Phys. Lett.* — 2004. — Nov. — Vol. 85, no. 22. — Pp. 5227–5229.
- [8] The effect of oxide precipitates on minority carrier lifetime in p-type silicon / J. D. Murphy, K. Bothe, M. Olmo et al. // *J. Appl. Phys.* — 2011. — Sep. — Vol. 110, no. 5. — P. 053713.
- [9] *Macdonald, D. H.* Iron detection in crystalline silicon by carrier lifetime measurements for arbitrary injection and doping / D. H. Macdonald, L. J. Geerligs, A. Azzizi // *J. Appl. Phys.* — 2004. — Feb. — Vol. 95, no. 3. — Pp. 1021–1028.
- [10] *Green, Martin A.* Improved silicon optical parameters at 25°C, 295 K and 300 K including temperature coefficients / Martin A. Green // *Prog. Photovoltaics Res. Appl.* — 2022. — Feb. — Vol. 30, no. 2. — Pp. 164–179.